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depositing a dopant-bearing metal over the semiconductor body in regions adjacent the gate; and

annealing the workpiece to cause diffusion of a dopant of the dopant-bearing metal into the semiconductor body.

43. (New) The method of claim 42 wherein depositing a gate dielectric material comprises depositing a high dielectric constant material.

44. (New) The method of claim 43 wherein depositing a gate material comprises depositing a metal.

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45. (New) The method of claim 42 wherein the dopant-bearing comprises at least one material selected from the group consisting of TiB_2 , ZrB_2 , and HfB_2 .

45. (New) The method of claim 42 wherein the dopant-bearing comprises at least one material selected from the group consisting of ZrP and TiP .

46. (New) The method of claim 42 wherein the dopant-bearing comprises at least one material selected from the group consisting of $ZrSb_2$, $TiSb_2$, and $HfSb_2$.

47. (New) The method of claim 42 wherein the dopant-bearing comprises an arsenide of Zr or an arsenide of Hf.